

# D3SB10 - D3SB80

**PRV : 100 - 800 Volts**  
**Io : 4.0 Amperes**

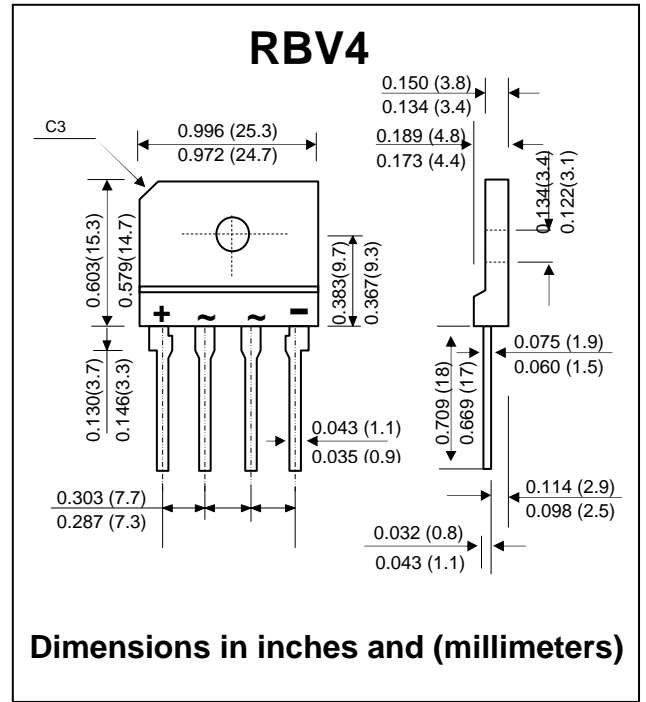
**FEATURES :**

- \* High current capability
- \* High surge current capability
- \* High reliability
- \* Low reverse current
- \* Low forward voltage drop
- \* Ideal for printed circuit board
- \* Very good heat dissipation
- \* **Pb / RoHS Free**

**MECHANICAL DATA :**

- \* Case : Reliable low cost construction utilizing molded plastic technique
- \* Epoxy : UL94V-O rate flame retardant
- \* Terminals : Plated lead solderable per MIL-STD-202, Method 208 guaranteed
- \* Polarity : Polarity symbols marked on case
- \* Mounting position : Any
- \* Weight : 4.28 grams

# SILICON BRIDGE RECTIFIERS



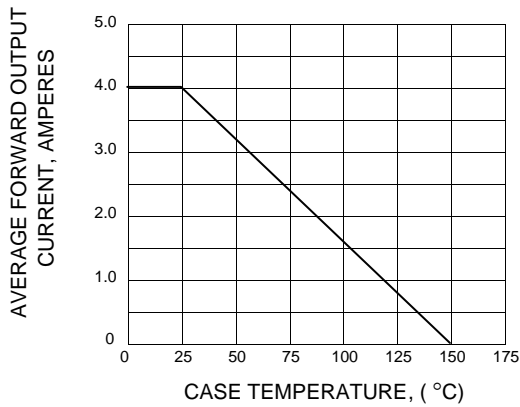
**MAXIMUM RATINGS AND ELECTRICAL CHARACTERISTICS**

Rating at 25 °C ambient temperature unless otherwise specific.  
 Single phase, half wave, 60 Hz, resistive or inductive load  
 For capacitive load, derate current by 20%

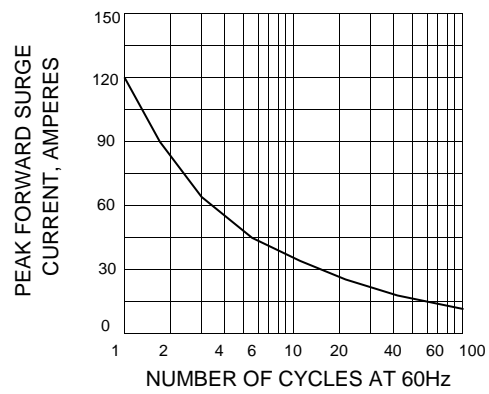
RATING	SYMBOL	D3S B10	D3S B20	D3S B40	D3S B60	D3S B80	UNIT
Maximum Reverse Voltage	V <sub>RM</sub>	100	200	400	600	800	V
Maximum Average Forward Current T <sub>c</sub> = 25°C	I <sub>F(AV)</sub>	4.0					A
Maximum Peak Forward Surge Current	I <sub>FSM</sub>	120					A
Maximum Forward Voltage per Diode at I <sub>F</sub> = 2.0 A	V <sub>F</sub>	1.05					V
Maximum Reverse Current at Reverse Voltage	I <sub>R</sub>	10					µA
Maximum Reverse Current at Reverse Voltage T <sub>a</sub> = 100 °C	I <sub>R(H)</sub>	100					µA
Operating Junction Temperature Range	T <sub>J</sub>	- 40 to + 150					°C
Storage Temperature Range	T <sub>STG</sub>	- 40 to + 150					°C

**RATING AND CHARACTERISTIC CURVES ( D3SB10 - D3SB80 )**

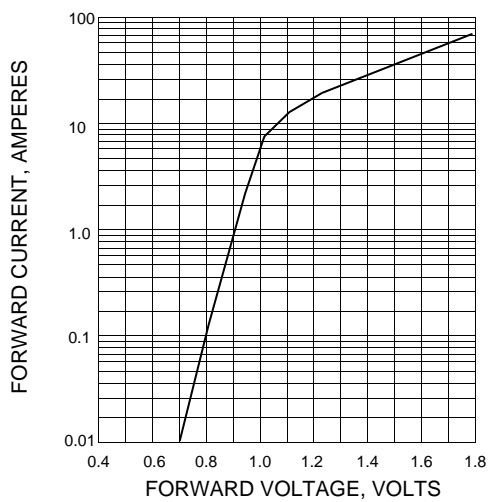
**FIG.1 - DERATING CURVE FOR OUTPUT RECTIFIED CURRENT**



**FIG.2 - MAXIMUM NON-REPETITIVE PEAK FORWARD SURGE CURRENT**



**FIG.3 - TYPICAL FORWARD CHARACTERISTICS**



**FIG.4 - TYPICAL REVERSE CHARACTERISTICS**

